ACT110-800E

AC Thyristor power switch

Rev.01 - 23 April 2025 Product data sheet

1. General description

AC Thyristor power switch in a SOT54(TO-92) plastic package with self-protective capabilities against low and high energy transients.

2. Features and benefits

- Common terminal on mounting base allows multiple ACTs on shared cooling pad
- Exclusive negative gate triggering
- Full cycle AC conduction
- High voltage capability
- Remote gate separates the gate driver from the effects of the load current
- Safe clamping of low energy over-voltage transients
- Self-protective turn-on during high energy voltage transients
- Surface-mountable package
- Very high noise immunity

3. Applications

- Fan motor circuits
- Pump motor circuits
- Lower-power highly inductive, resistive and safety loads
- Contactors, circuit breakers, valves, dispensers and door locks

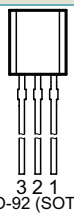
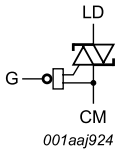
4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes	Values			Unit
Absolute maximum rating							
V_{DRM}	repetitive peak off-state voltage			800			V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{lead} \leq 47$ °C; Fig. 1; Fig. 2; Fig. 3		1.5			A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25$ °C; $t_p = 20$ ms; Fig. 4; Fig. 5		16			A
		full sine wave; $T_{j(init)} = 25$ °C; $t_p = 16.7$ ms		17.6			A
T_j	operating junction temperature			-40 to 125			°C
V_{PP}	peak pulse voltage	$T_j = 25$ °C; non-repetitive, off-state; Fig. 6		2.5			kV
Symbol	**Parameter**	**Conditions**	**Notes**	**Min**	**Typ**	**Max**	**Unit**
Static characteristics							
I_{GT}	gate trigger current	$V_D = 12$ V; $I_T = 0.1$ A; LD+ G-; $T_j = 25$ °C; Fig. 8		-	-	10	mA
		$V_D = 12$ V; $I_T = 0.1$ A; LD- G-; $T_j = 25$ °C; Fig. 8		-	-	10	mA
I_H	holding current	$V_D = 12$ V; $T_j = 25$ °C; Fig. 10		-	-	20	mA
V_T	on-state voltage	$I_T = 1.1$ A; $T_j = 25$ °C; Fig. 11		-	-	1.35	V
V_{CL}	clamping voltage	$I_{CL} = 0.1$ mA; $t_p = 1$ ms		850	-	-	V

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	CM	common	 TO-92 (SOT54)	 001aaj924
2	G	gate		
3	LD	load		

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
ACT110-800E	TO92	ACT110-800E, 412	Bulk	1000	TO92L	10-May-2021

7. Marking

Table 4. Marking codes

Type number	Marking codes
ACT110-800E	110-8E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Max	Unit
V_{DRM}	repetitive peak off-state voltage			800	V
V_{RRM}	repetitive peak reverse voltage			800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{lead} \leq 47$ °C; Fig 1; Fig 2; Fig 3		1.5	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25$ °C; $t_p = 20$ ms; Fig 4; Fig 5		16	A
		full sine wave; $T_{j(init)} = 25$ °C; $t_p = 16.7$ ms		17.6	A
I^2t	I^2t for fusing	$t_p = 10$ ms; SIN		1.28	A^2s
dI_T/dt	rate of rise of on-state current	$I_G = 20$ mA		100	A/µs
I_{GM}	peak gate current	t = 20 µs		1	A
V_{GM}	peak gate voltage	t = 20 µs		15	V
P_{GM}	peak gate power			0.1	W
T_{stg}	storage temperature			-40 to 150	°C
T_j	operating junction temperature			-40 to 125	°C
V_{PP}	peak pulse voltage	$T_j = 25$ °C; non-repetitive, off-state; Fig. 6		2.5	kV

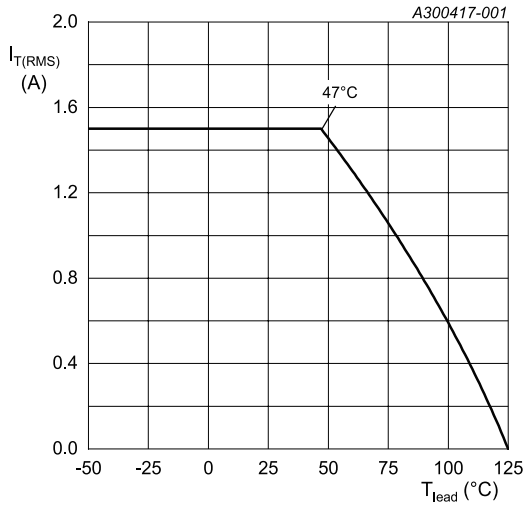
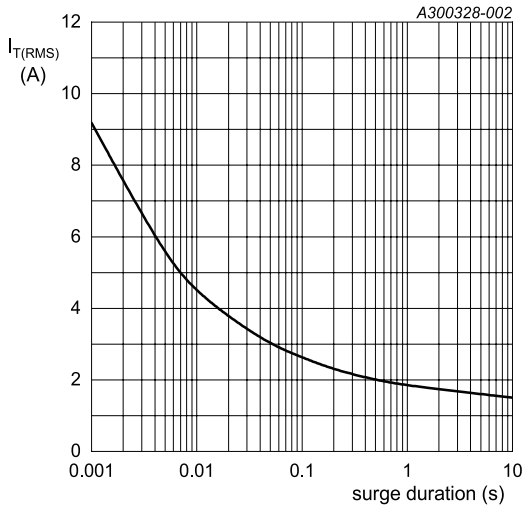
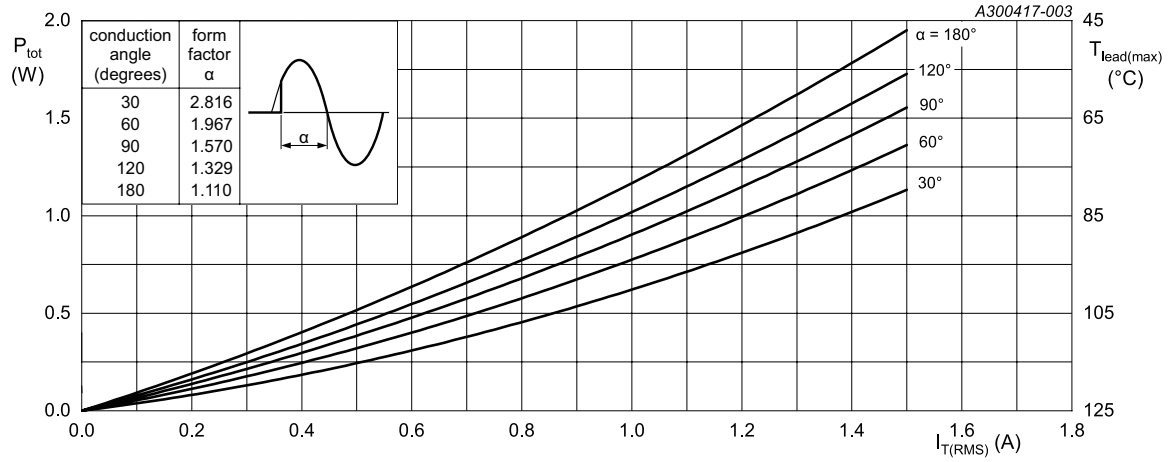


Fig. 1. RMS on-state current as a function of lead temperature; maximum values



f = 50 Hz; T_{lead} = 47 °C

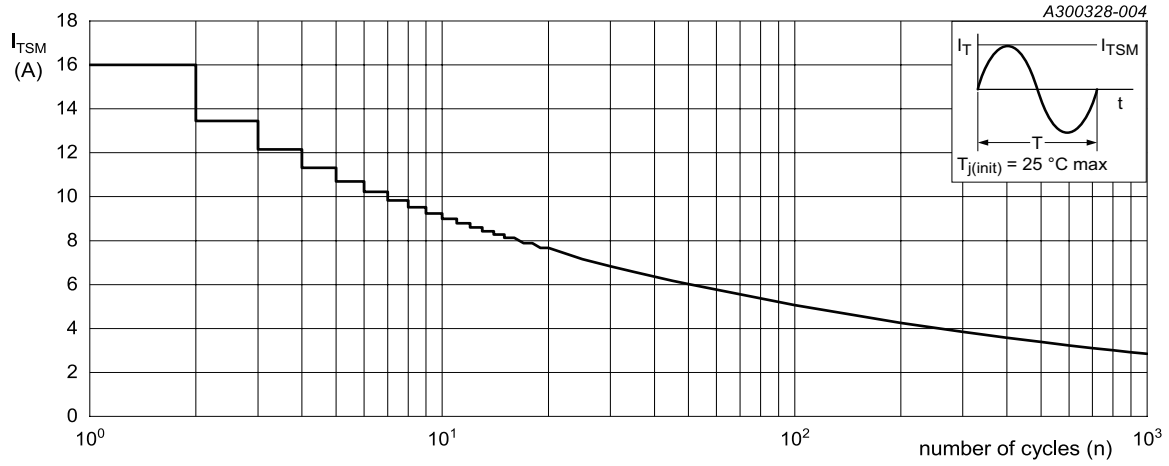
Fig. 2. RMS on-state current as a function of surge duration; maximum values



α = conduction angle

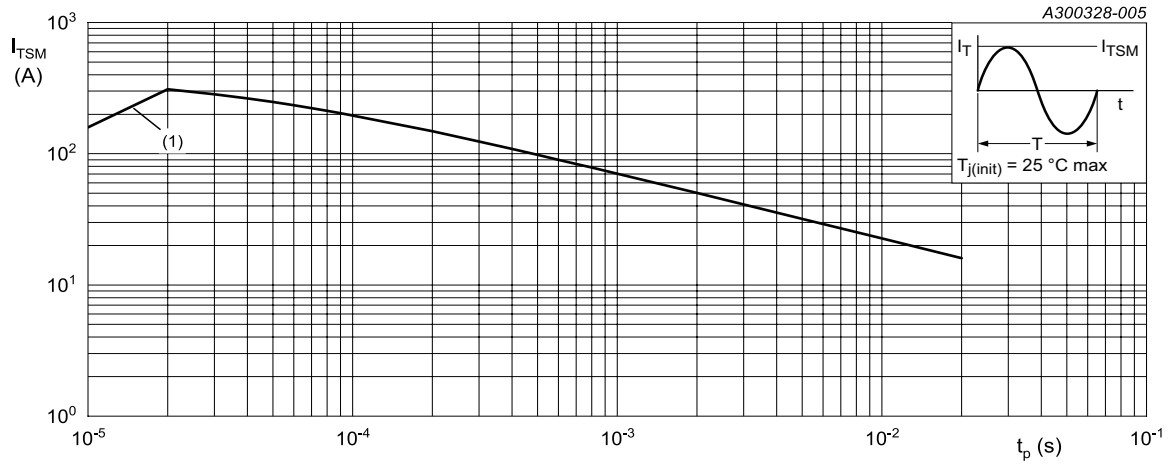
a = form factor = $I_{T(RMS)}$ / $I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



t_p ≤ 20 ms

(1) dI_T/dt limit

Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

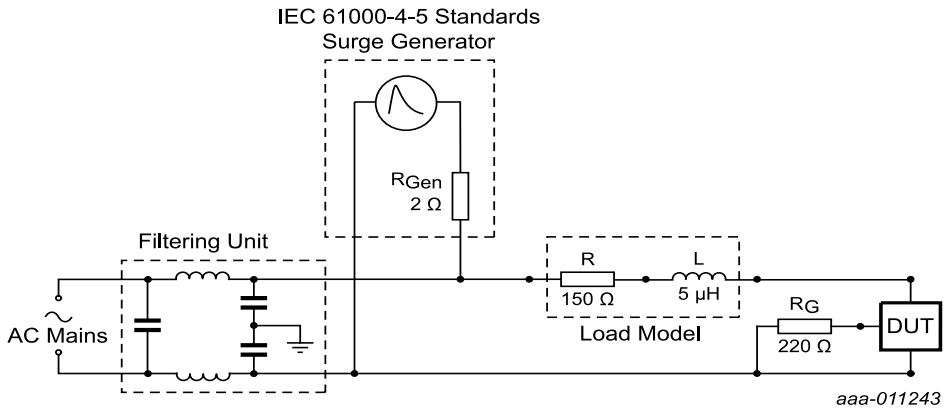


Fig. 6. Test circuit for inductive and resistive loads with conditions equivalent to IEC 61000-4-5

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j\text{-}lead)}$	thermal resistance from junction to lead	full cycle; Fig. 7		-	40	-	K/W
$R_{th(j\text{-}a)}$	thermal resistance from junction to ambient free air	in free air		-	150	-	K/W

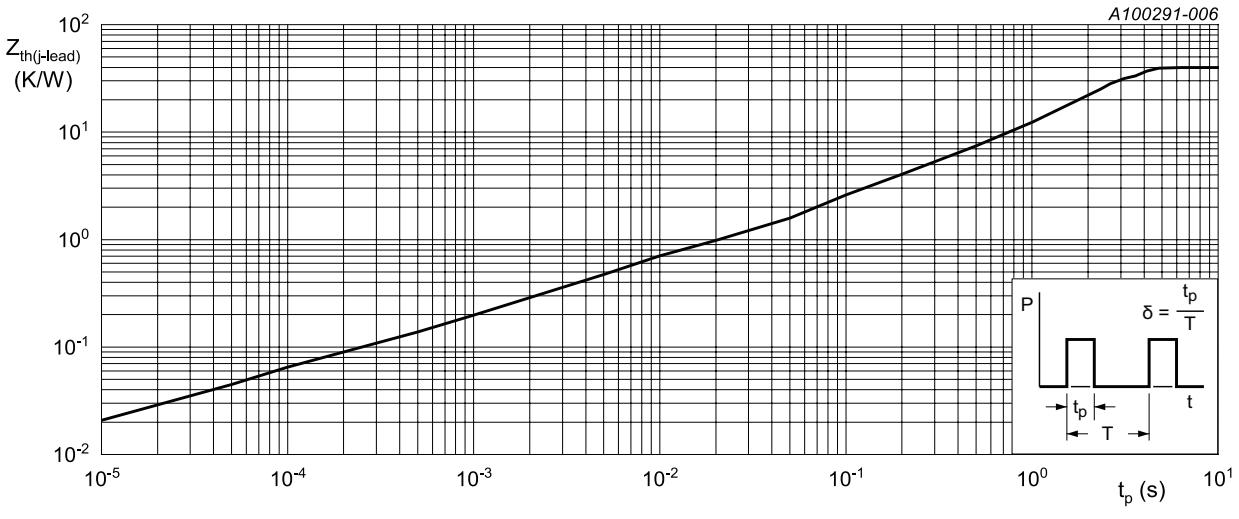
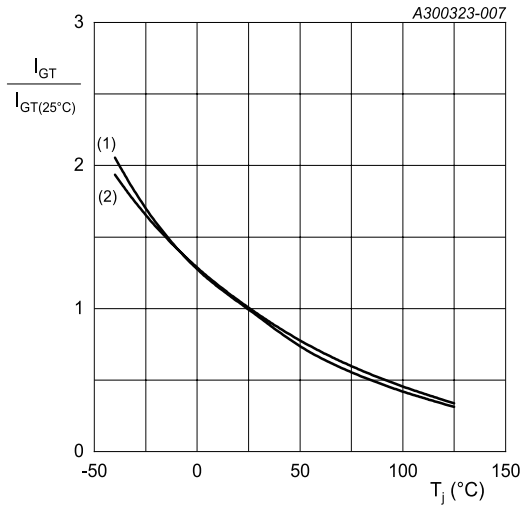


Fig. 7. Transient thermal impedance from junction to lead as a function of pulse width

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
Static characteristics							
I_{GT}	gate trigger current	V_D = 12 V; I_T = 0.1 A; LD+ G-; T_j = 25 °C; Fig. 8		-	-	10	mA
		V_D = 12 V; I_T = 0.1 A; LD- G-; T_j = 25 °C; Fig. 8		-	-	10	mA
I_L	latching current	V_D = 12 V; I_G = 0.1 A; LD+ G-; T_j = 25 °C; Fig. 9		-	-	25	mA
		V_D = 12 V; I_G = 0.1 A; LD- G-; T_j = 25 °C; Fig. 9		-	-	20	mA
I_H	holding current	V_D = 12 V; T_j = 25 °C; Fig. 10		-	-	20	mA
V_T	on-state voltage	I_T = 1.1 A; T_j = 25 °C; Fig. 11		-	-	1.35	V
V_{GT}	gate trigger voltage	V_D = 12 V; I_T = 0.1 A; T_j = 25 °C; Fig. 12		-	-	1	V
		V_D = 400 V; I_T = 0.1 A; T_j = 125 °C		0.15	-	-	V
I_D	off-state current	V_D = 800 V; T_j = 25 °C		-	-	10	µA
		V_D = 800 V; T_j = 125 °C		-	-	2	mA
I_R	reverse current	V_R = 800 V; T_j = 25 °C		-	-	10	µA
		V_R = 800 V; T_j = 125 °C		-	-	2	mA
V_{CL}	clamping voltage	I_{CL} = 0.1 mA; t_p = 1 ms		850	-	-	V
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit		2000	-	-	V/µs
dI_{com}/dt	rate of change of commutating current	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 1.5 A; dV_{com}/dt = 20 V/µs; (snubberless condition); gate open circuit		0.5	-	-	A/ms



(1) LD+ G-
(2) LD- G-

Fig. 8. Normalized gate trigger current as a function of junction temperature

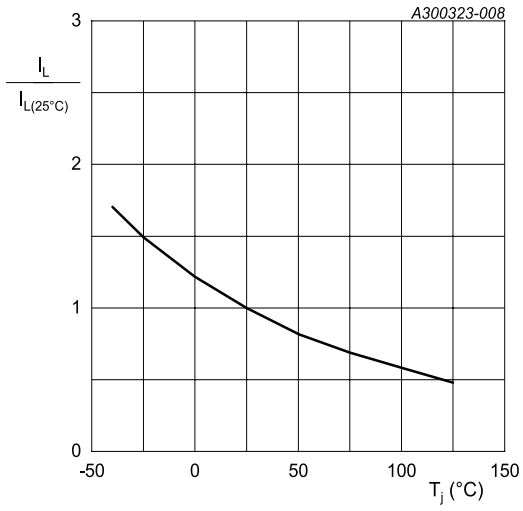


Fig. 9. Normalized latching current as a function of junction temperature

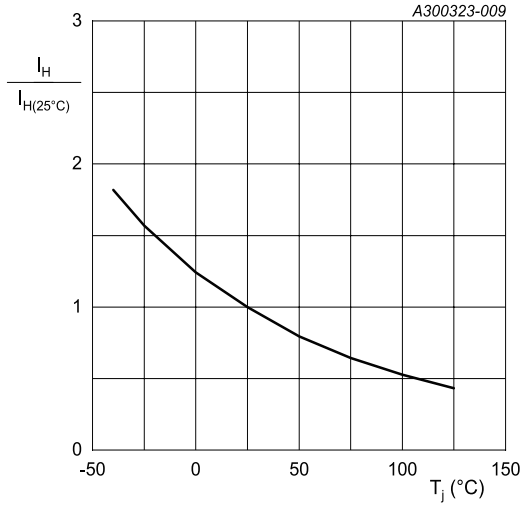
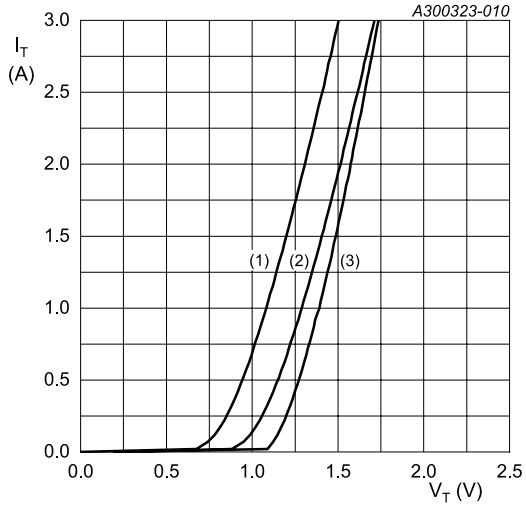


Fig. 10. Normalized holding current as a function of junction temperature



V_o = 0.999 V; R_s = 0.2667 Ω
(1) T_j = 125 °C; typical values
(2) T_j = 125 °C; maximum values
(3) T_j = 25 °C; maximum values

Fig. 11. On-state current as a function of on-state voltage

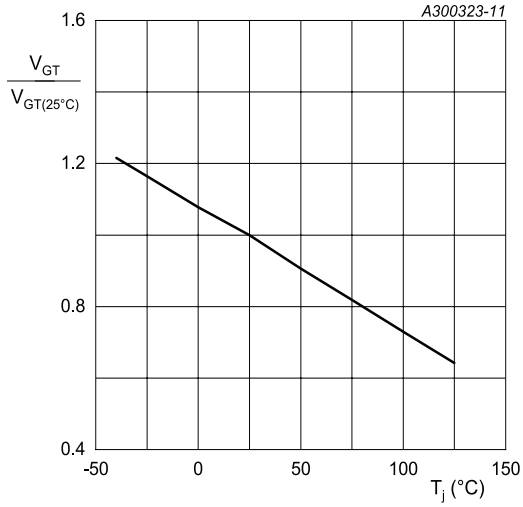
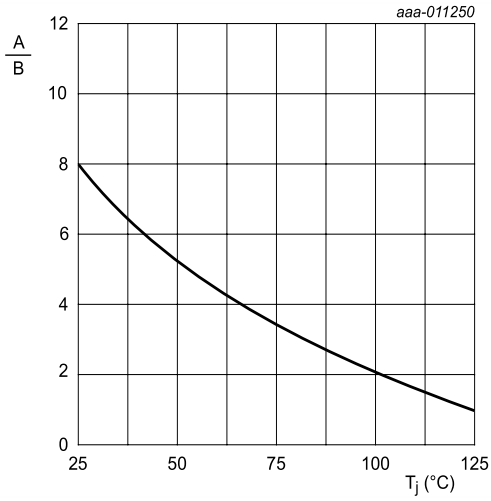
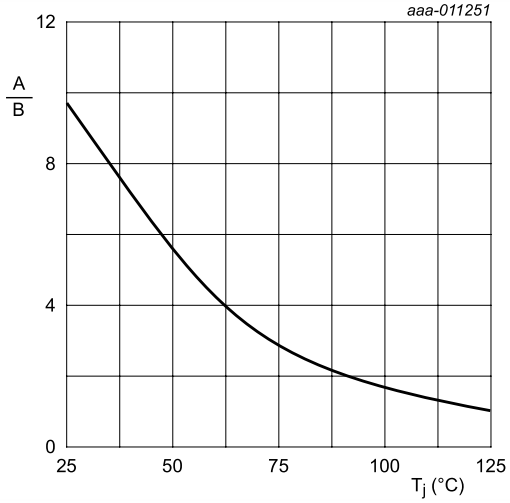


Fig. 12. Normalized gate trigger voltage as a function of junction temperature



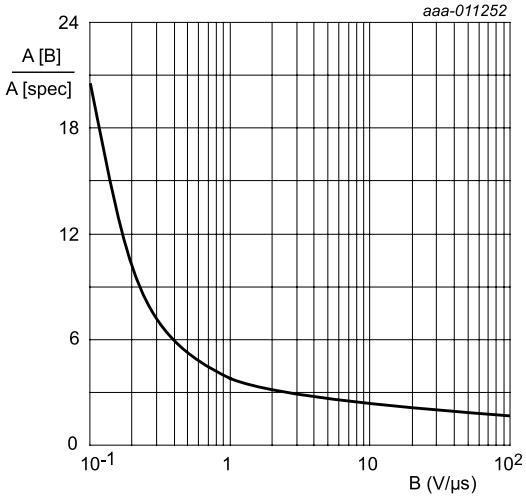
A = dV_D/dt at condition T_j °C
B = dV_D/dt at condition T_j [125] °C

Fig. 13. Normalized rate of rise of off-state voltage as a function of junction temperature



A = dI_{com}/dt at condition T_j °C
B = dI_{com}/dt at condition T_j [125] °C
V_D = 400 V

Fig. 14. Normalized critical rate of rise of commutating current as a function of junction temperature

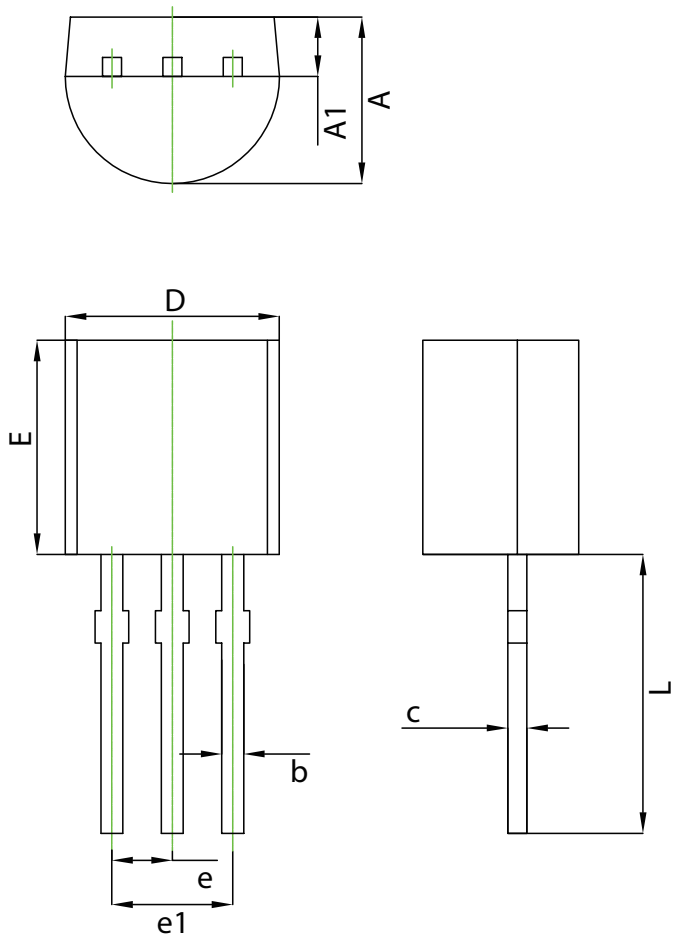


A [B] = dI_{com}/dt at condition B, dV_{com}/dt
A [spec] is the data sheet value for dI_{com}/dt
turn-off time is less than 20 ms

Fig. 15. Normalized critical rate of change of commutating current as a function of critical rate of change of commutating voltage; minimum values

11. Package outline

TO92L 412



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	3.300	3.700	0.130	0.146
A1	1.100	1.400	0.043	0.055
b	0.380	0.550	0.015	0.022
c	0.360	0.510	0.014	0.020
D	4.300	4.700	0.169	0.185
E	4.300	4.700	0.169	0.185
e	1.270 TYP.		0.050 TYP.	
e1	2.440	2.640	0.096	0.104
L	14.100	14.500	0.555	0.571

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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